

SINGLE SIDED DC MICROSTRIP DETECTOR

SILICON DETECTOR TYPE: DC coupled ion implanted totally depleted silicon microstrip detector which can be tailored for single sided p-n devices or n-n double sided devices. Microstrip device with a multi-guard ring design for high radiation environment operation.

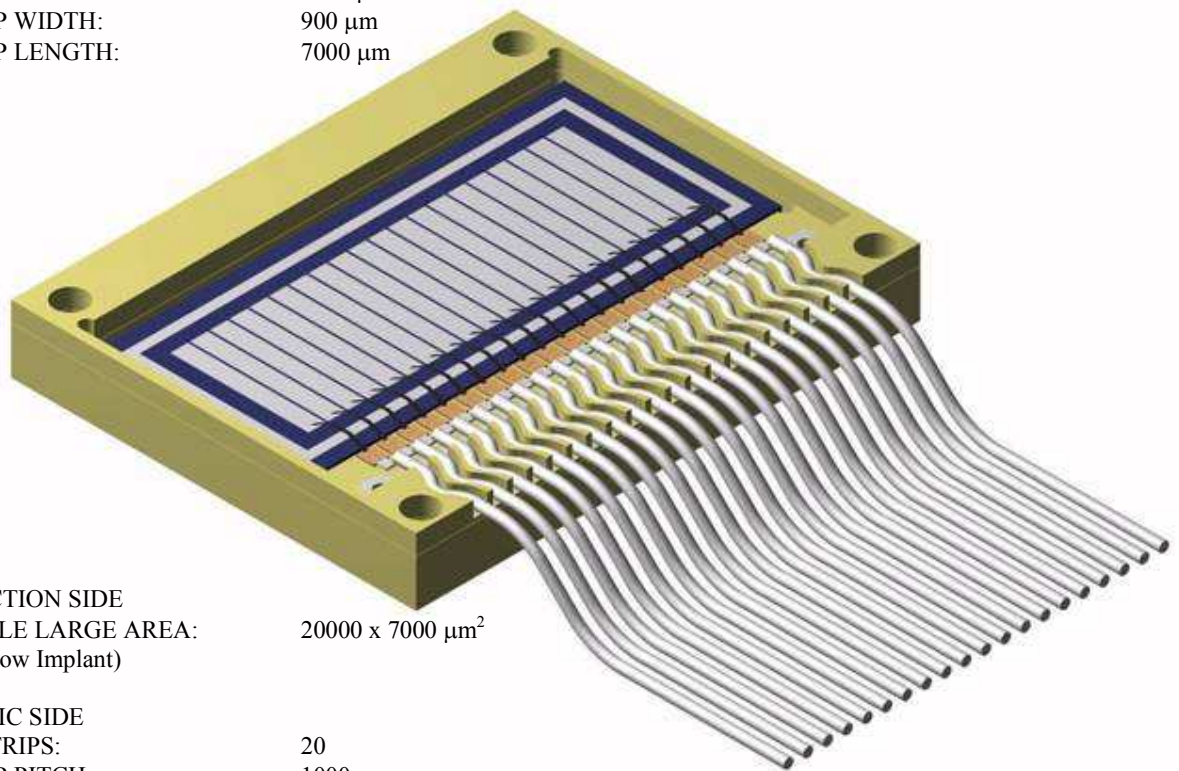
TECHNOLOGY: 3 inch wafer technology for n-n design
4 inch wafer technology for p-n design

DESIGN: Microstrip device with a multi-guard ring design for high radiation environment operation.

THICKNESS: 65 -1000 μm

P-N DEVICE:

JUNCTION SIDE
 N° STRIPS: 20
 STRIP PITCH: 1000 μm
 STRIP WIDTH: 900 μm
 STRIP LENGTH: 7000 μm



N-N DEVICE:

JUNCTION SIDE
 SINGLE LARGE AREA: 20000 x 7000 μm^2
 (Shallow Implant)

OHMIC SIDE
 N° STRIPS: 20
 STRIP PITCH: 1000 μm
 STRIP WIDTH: 900 μm
 STRIP LENGTH: 7000 μm

CHIP DIMENSIONS: 20000 x 7000 μm^2

PACKAGE: The chip is recessed in a transmission FR4 PCB
 Dimensions = 18.5 x 25.5 x 1.0 mm³
 Mounting holes, \varnothing 1.6 mm

CONNECTION: Junkosha Miniature Coaxial cable

MINIMUM ACCEPTANCE 100 %

(This detector is also available as a standard single sided p-n 32 channel chip only detector)

QUALITY ASSURANCE :ISO9001

